

2SC4502

Silicon NPN epitaxial planer type

For mtermediate frequency amplification

Features

- High transition frequency f_T .
- Large collector power dissipation P_C .
- Allowing supply with the radial taping.

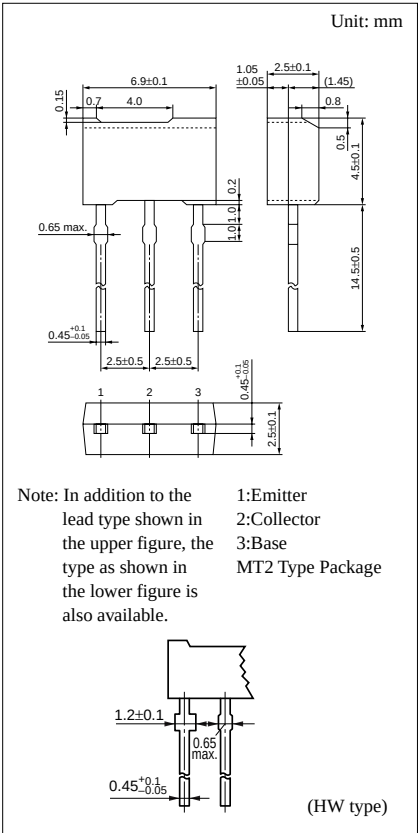
Absolute Maximum Ratings (Ta=25°C)

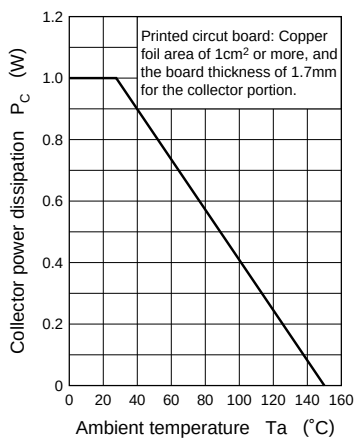
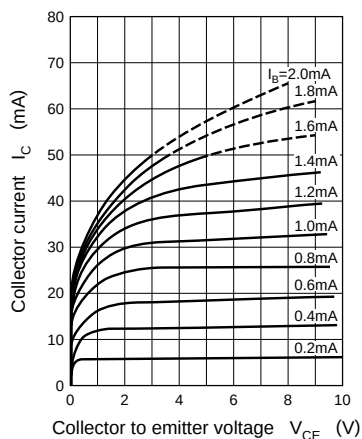
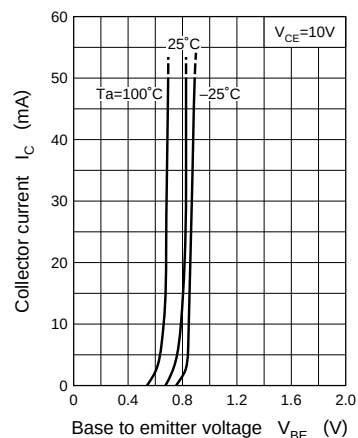
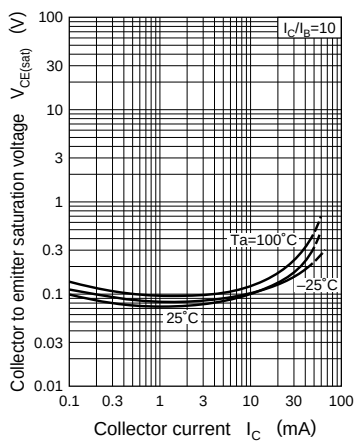
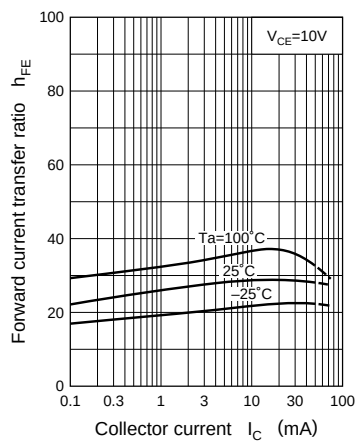
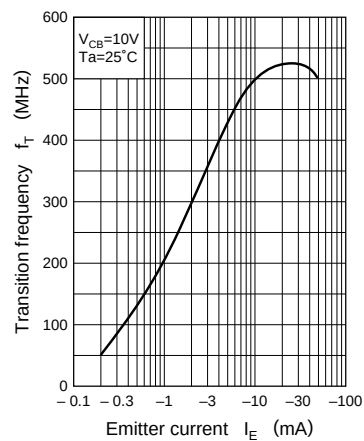
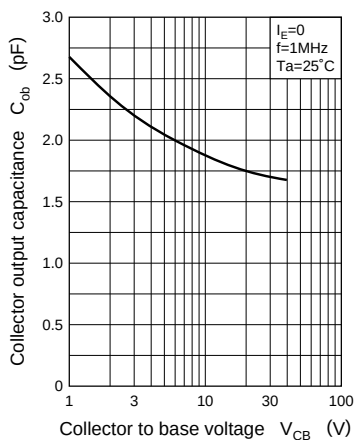
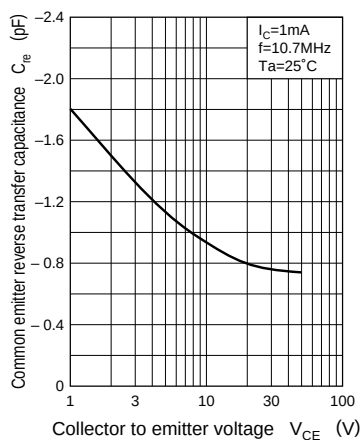
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	50	V
Collector to emitter voltage	V_{CEO}	45	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	50	mA
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$			100	nA
Collector to base voltage	V_{CBO}	$I_C = 100\mu A, I_E = 0$	50			V
Collector to emitter voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	45			V
Emitter to base voltage	V_{EBO}	$I_E = 100\mu A, I_C = 0$	4			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 10V, I_C = 10\mu A$	20		100	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$			0.4	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$	300			MHz
Common emitter reverse transfer capacitance	C_{re}	$V_{CB} = 10V, I_E = -1mA, f = 10.7MHz$			1.5	pF
Power gain	PG	$V_{CB} = 10V, I_E = -10mA, f = 58MHz$	22		30	dB



$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$  $C_{re} - V_{CE}$  $PG - I_E$ 